

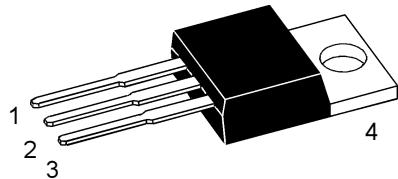
High Voltage IGBT

IXGP 2N100
IXGP 2N100A

V_{CES}	I_{C90}	$V_{CE(SAT)}$
1000 V	2.0 A	2.7 V
1000 V	2.0 A	3.5 V

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{GCR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_c = 25^\circ\text{C}$	4	A
I_{C90}	$T_c = 90^\circ\text{C}$	2	A
I_{CM}	$T_c = 25^\circ\text{C}$, 1 ms	8	A
SSOA (RBSSOA)	$V_{GE} = 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 150\Omega$ Clamped inductive load	$I_{CM} = 6$ @ 0.8 V_{CES}	A
P_c	$T_c = 25^\circ\text{C}$	25	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{STG}		-55 ... +150	$^\circ\text{C}$
Weight		4	g
Max. Lead Temperature for Soldering (1.6mm from case for 10s)		300	$^\circ\text{C}$

TO-220



1 = Gate 2 = Collector
3 = Emitter 4 = Collector

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_c = 25\mu\text{A}$, $V_{GE} = 0 \text{ V}$	1000		V
$V_{GE(th)}$	$I_c = 25\mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		10 μA 200 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			± 50 nA
$V_{CE(sat)}$	$I_c = I_{C90}$, $V_{GE} = 15 \text{ V}$	IXGP2N100 IXGP2N100A		2.7 V 3.5 V

Features

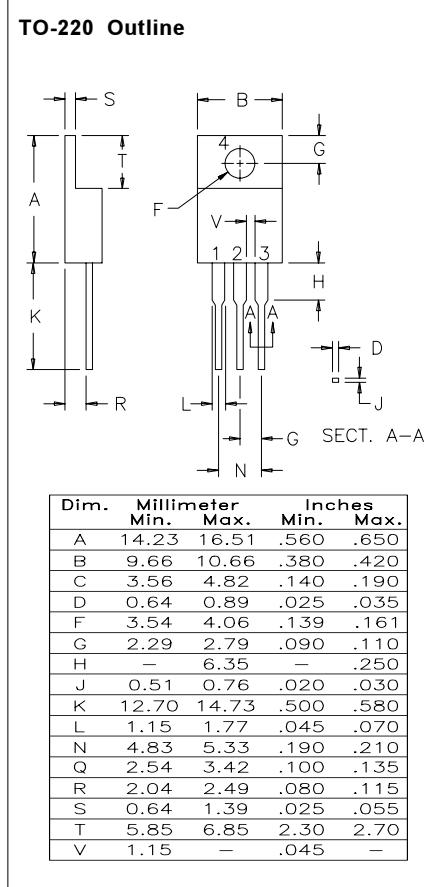
- International standard package
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity

Applications

- Capacitor discharge
- Anode triggering of thyristors
- DC choppers
- Switched-mode and resonant-mode power supplies.

Symbol	Test Conditions ($T_j = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values			
		Min.	Typ.	Max.	
g_{fs}	$I_c = I_{c90}, V_{CE} = 10 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$	0.7	1.5	S	
C_{les}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	101	pF		
C_{oes}		12	pF		
C_{res}		1.8	pF		
Q_g	$I_c = I_{c90}, V_{GE} = 15 \text{ V}, V_{CE} = 0.5 V_{CES}$	7.8	nC		
Q_{ge}		1.5	nC		
Q_{gc}		4.2	nC		
$t_{d(on)}$	Inductive load, $T_j = 25^\circ\text{C}$	15	ns		
t_{ri}	$I_c = I_{c90}, V_{GE} = 15 \text{ V}$	20	ns		
$t_{d(off)}$	$R_G = 150 \Omega$	300	600	ns	
t_{fl}	$V_{CLAMP} = 0.8 V_{CES}$	IXGP2N100	560	1000	ns
		IXGP2N100A	180	360	ns
E_{off}	Note 1	IXGP2N100	0.56	1.2	mJ
		IXGP2N100A	0.26	0.6	mJ
$t_{d(on)}$	Inductive load, $T_j = 125^\circ\text{C}$	15	ns		
t_{ri}	$I_c = I_{c90}, V_{GE} = 15 \text{ V}$	25	ns		
$E_{(on)}$	$R_G = R_{(off)} = 150 \Omega$	0.3	mJ		
$t_{d(off)}$	$V_{CLAMP} = 0.8 V_{CES}$	400	ns		
t_{fl}	Note 1	IXGP2N100	800	ns	
		IXGP2N100A	360	ns	
		IXGP2N100	1.0	mJ	
E_{off}		IXGP2N100A	0.5	mJ	
R_{thJC}			5	KW	
R_{thJA}			110	KW	

Notes: 1. Switching times may increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, higher T_j or increased R_G .



The data herein reflects the advanced objective technical specification and characterization data from engineering lots.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025